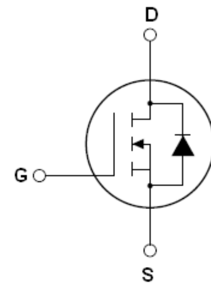
SILIKRON

SSF6808

Feathers:

- Advanced trench process technology
- Ultra low Rdson, typical 6mohm
- High avalanche energy, 100% test
- Fully characterized avalanche voltage and current

ID =84A
BV=68V
Rdson=8mohm

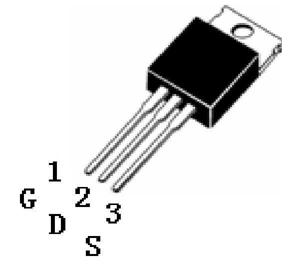


Description:

The SSF6808 is a new generation of middle voltage and high current N–Channel enhancement mode trench power MOSFET. This new technology increases the device reliability and electrical parameter repeatability. SSF6808 is assembled in high reliability and qualified assembly house.

Application:

- Power switching application



SSF6808 TOP View (TO220)

Absolute Maximum Ratings

	Parameter	Max.	Units
I_D@T_c=25˚C	Continuous drain current,VGS@10V	84	A
I_D@T_c=100℃	Continuous drain current,VGS@10V	76	
I_{DM}	Pulsed drain current ①	310	
P_D@T_C=25℃	Power dissipation	181	W
	Linear derating factor	1.5	W/˚C
V_{GS}	Gate-to-Source voltage	±20	V
dv/dt	Peak diode recovery voltage	31	v/ns
E_{AS}	Single pulse avalanche energy ②	400	mJ
E_{AR}	Repetitive avalanche energy	TBD	
T_J T_{STG}	Operating Junction and Storage Temperature Range	–55 to +175	℃

Thermal Resistance

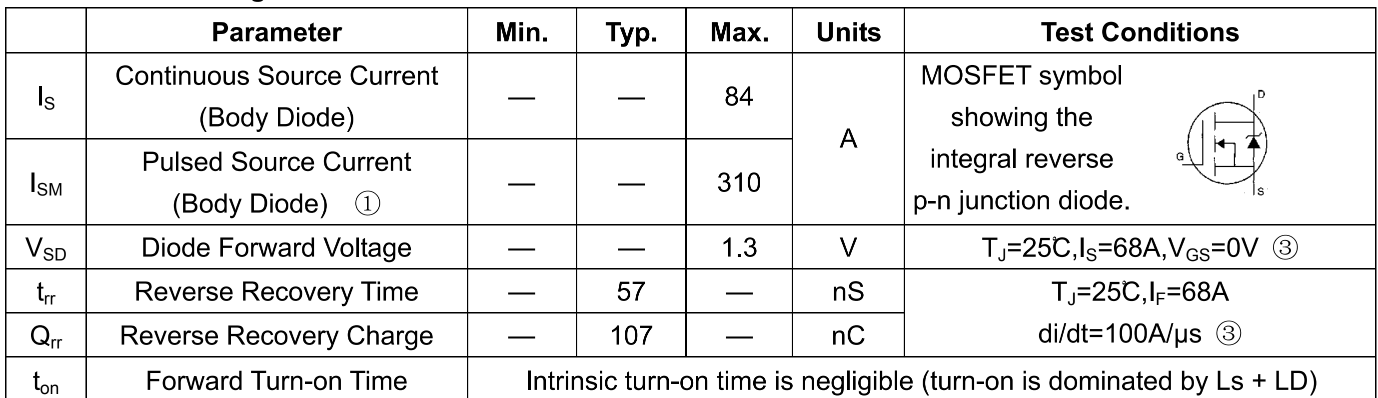
	Parameter	Min.	Typ.	Max.	Units
$R_{θJC}$	Junction-to-case	—	0.83	—	℃/W
$R_{θJA}$	Junction-to-ambient	—	—	62	

Electrical Characteristics @TJ=25 ℃ (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Test Conditions
BV_{DSS}	Drain-to-Source breakdown voltage	68	—	—	V	V_{GS}=0V,I_D=250μA
$R_{DS(on)}$	Static Drain-to-Source on-resistance	—	5	8	mΩ	V_{GS}=10V,I_D=30A
$V_{GS(th)}$	Gate threshold voltage	2.0	—	4.0	V	V_{DS}=V_{GS},I_D=250μA
I_{DSS}	Drain-to-Source leakage current	—	—	2	μA	V_{DS}=68V,V_{GS}=0V
		—	—	10		V_{DS}=68V, V_{GS}=0V,T_J=150℃

I_{GSS}	Gate-to-Source forward leakage	—	—	100	nA	V_{GS}=20V
	Gate-to-Source reverse leakage	—	—	-100		V_{GS}=-20V
Q_g	Total gate charge	—	90	—	nC	I_D=30A
Q_{gs}	Gate-to-Source charge	—	18	—		V_{DD}=30V
Q_{gd}	Gate-to-Drain("Miller") charge	—	28	—		V_{GS}=10V
$t_{d(on)}$	Turn-on delay time	—	18.2	—	nS	V_{DD}=30V
t_r	Rise time	—	15.6	—		I_D=2A ,R_L=15Ω
$t_{d(off)}$	Turn-Off delay time	—	70.5	—		R_G=2.5Ω
t_f	Fall time	—	13.8	—		V_{GS}=10V
C_{iss}	Input capacitance	—	3150	—	pF	V_{GS}=0V
C_{oss}	Output capacitance	—	300	—		V_{DS}=25V
C_{rss}	Reverse transfer capacitance	—	240	—		f=1.0MHZ

Source-Drain Ratings and Characteristics



	Parameter	Min.	Typ.	Max.	Units	Test Conditions
I_S	Continuous Source Current (Body Diode)	—	—	84	A	MOSFET symbol showing the integral reverse p-n junction diode.
I_{SM}	Pulsed Source Current (Body Diode) ①	—	—	310		
V_{SD}	Diode Forward Voltage	—	—	1.3	V	T_J=25℃,I_S=68A,V_{GS}=0V ③
t_{rr}	Reverse Recovery Time	—	57	—	nS	T_J=25℃,I_F=68A di/dt=100A/μs ③
Q_{rr}	Reverse Recovery Charge	—	107	—	nC	
t_{on}	Forward Turn-on Time	Intrinsic turn-on time is negligible (turn-on is dominated by Ls + LD)				

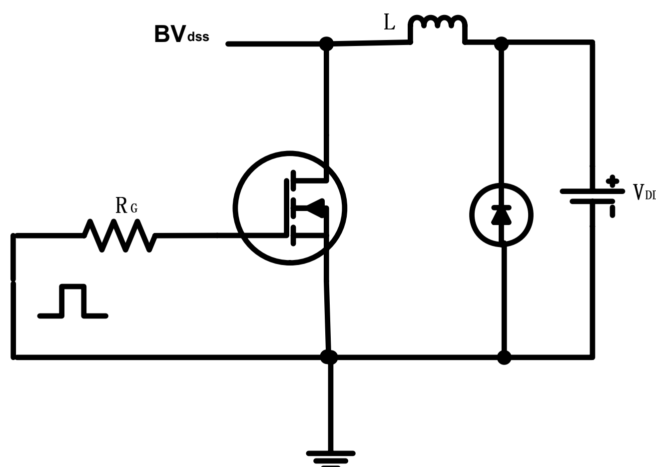
Notes:

① Repetitive rating; pulse width limited by max junction temperature.

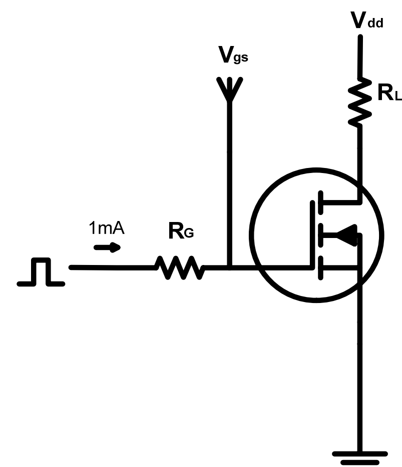
② Test condition: L =0.3mH, ID = 37A, VDD = 30V

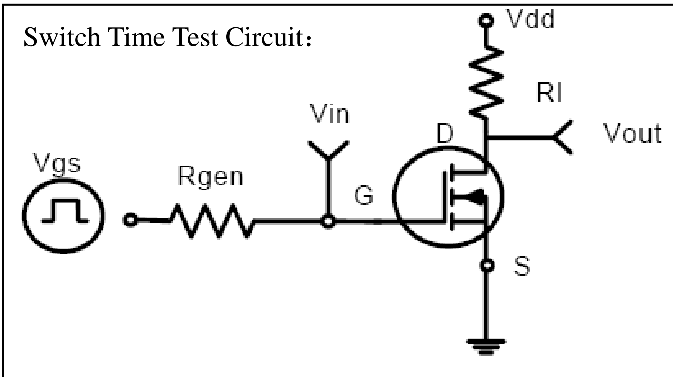
③ Pulse width≤300μS, duty cycle≤1.5% ; RG = 25Ω Starting TJ = 25°C

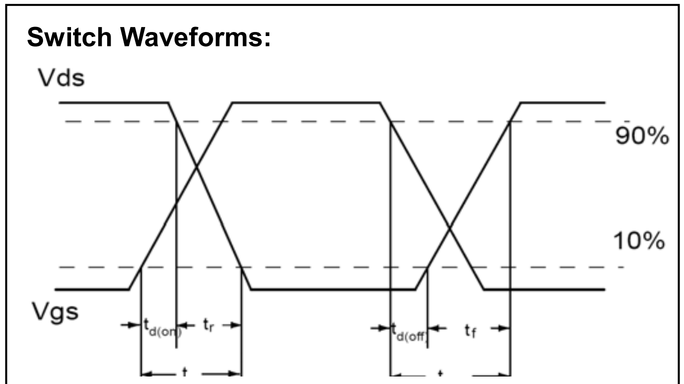
EAS test circuit:

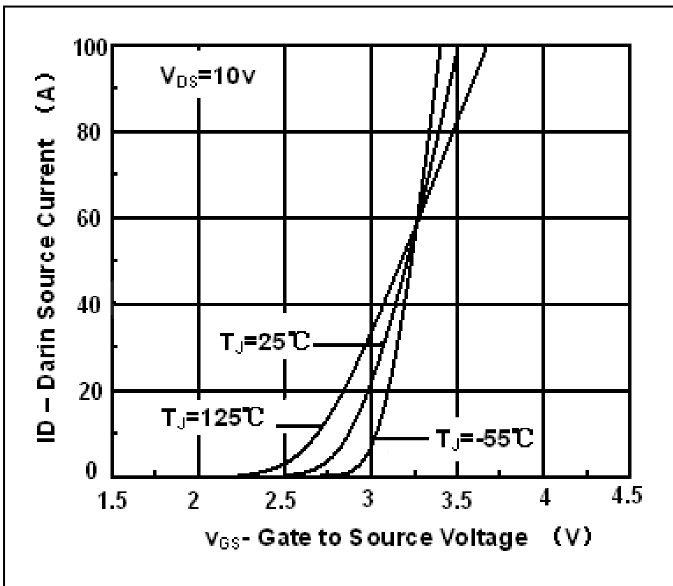


Gate charge test circuit:

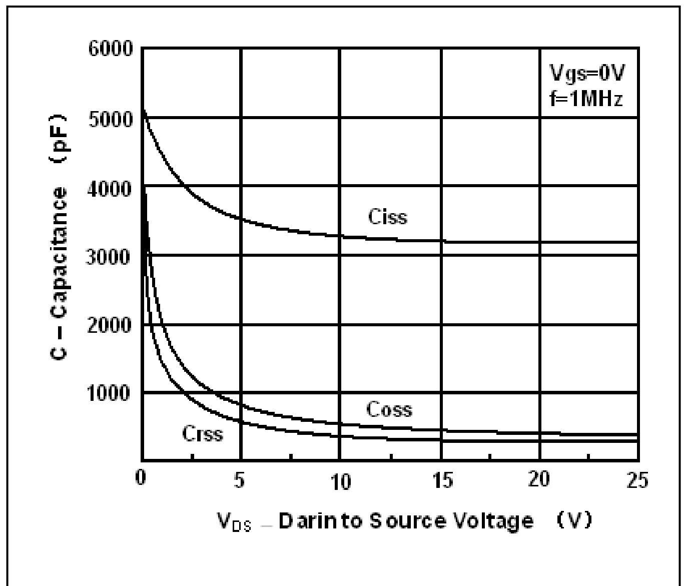




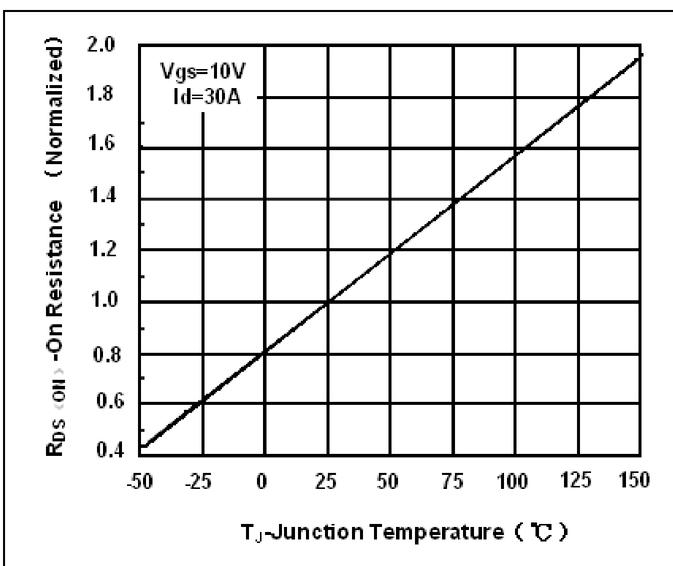




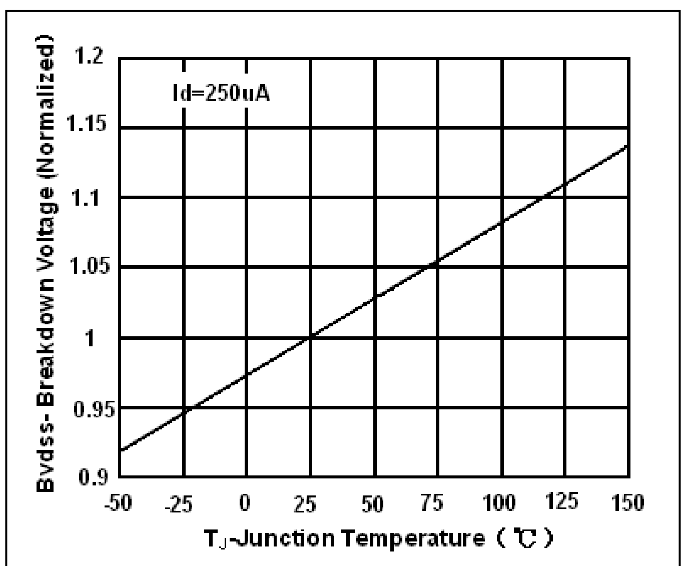
Transfer Characteristic



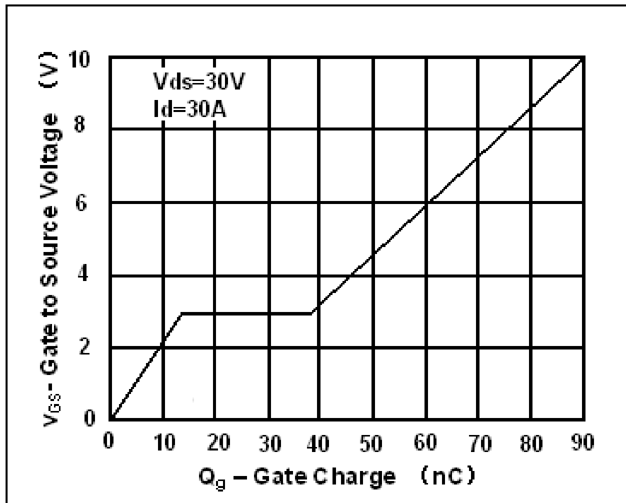
Capacitance



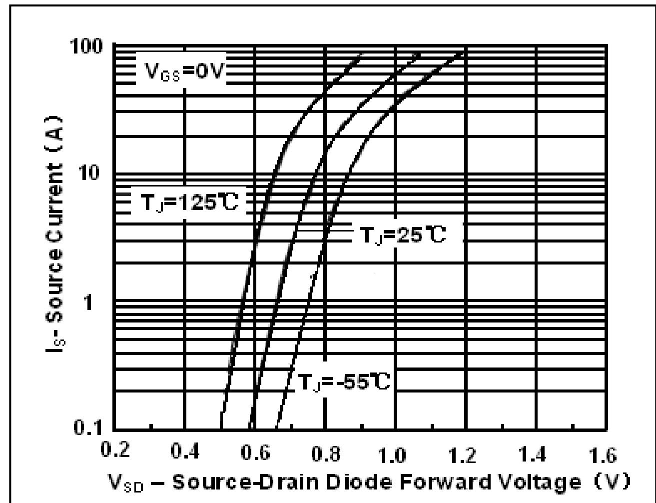
On Resistance vs. Junction Temperature



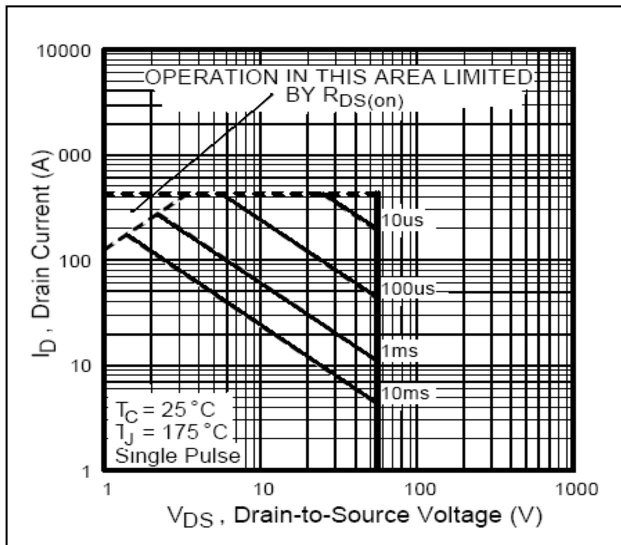
Breakdown Voltage vs. Junction Temperature



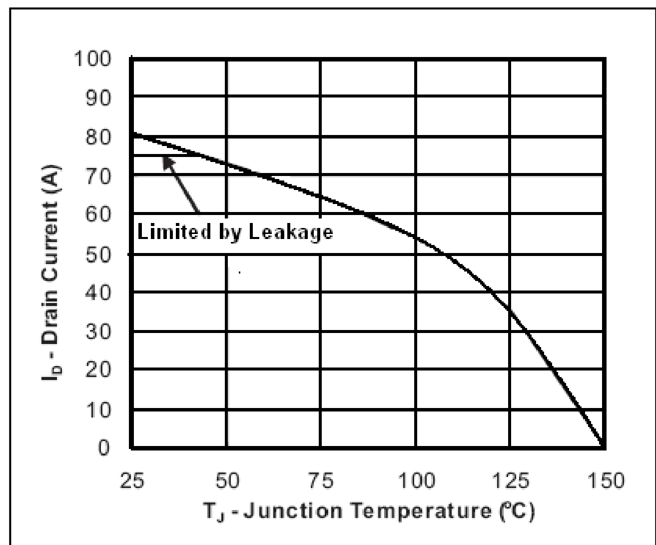
Gate Charge



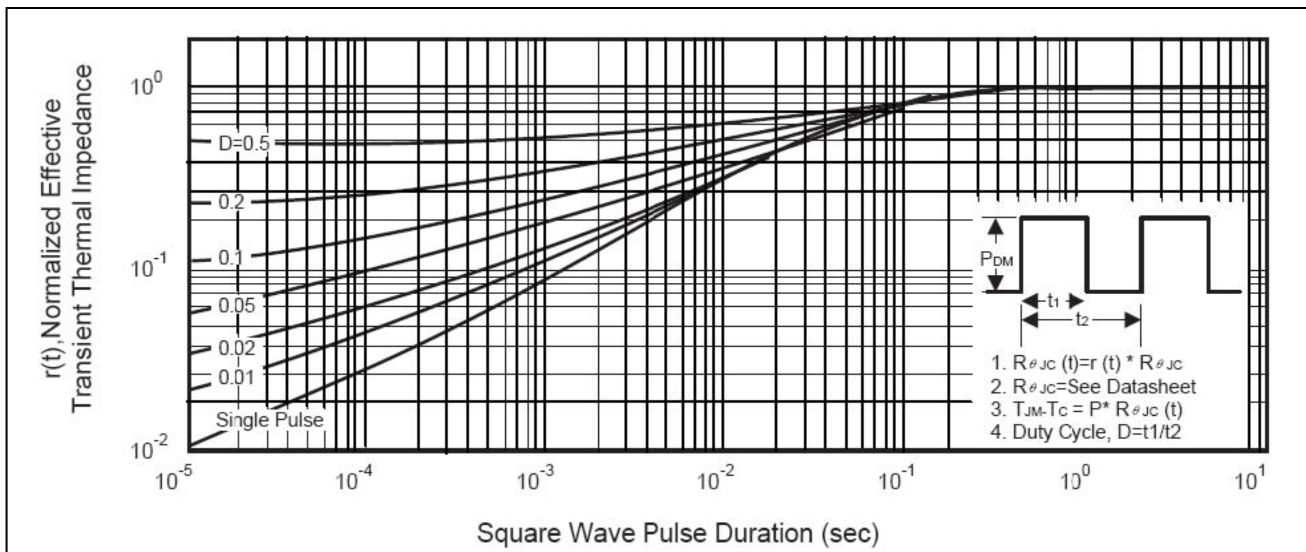
Source-Drain Diode Forward Voltage



Safe Operation Area

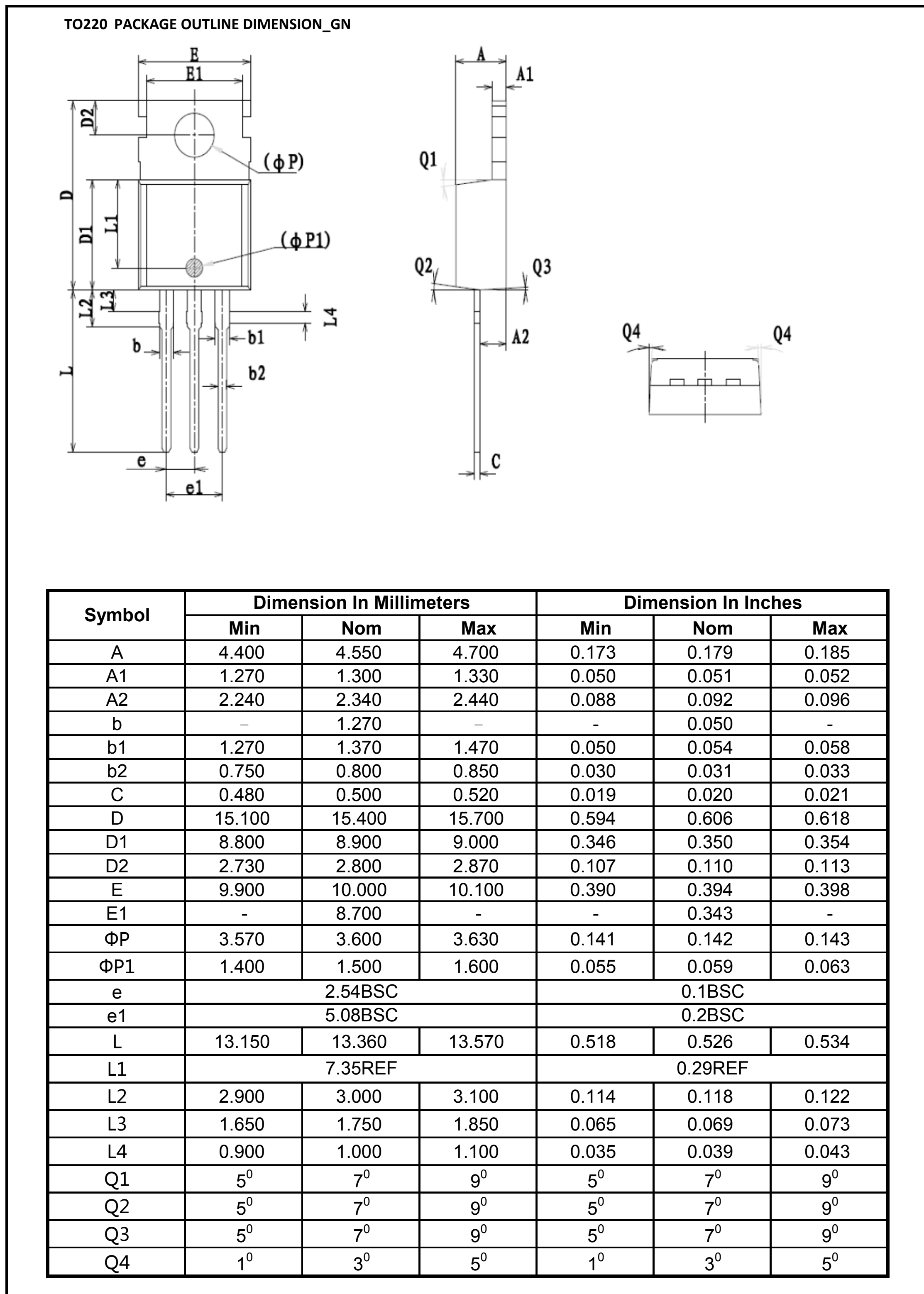


Max Drain Current vs. Junction Temperature



Transient Thermal Impedance Curve

Mechanical Data：



Symbol	Dimension In Millimeters			Dimension In Inches		
	Min	Nom	Max	Min	Nom	Max
A	4.400	4.550	4.700	0.173	0.179	0.185
A1	1.270	1.300	1.330	0.050	0.051	0.052
A2	2.240	2.340	2.440	0.088	0.092	0.096
b	–	1.270	–	-	0.050	-
b1	1.270	1.370	1.470	0.050	0.054	0.058
b2	0.750	0.800	0.850	0.030	0.031	0.033
C	0.480	0.500	0.520	0.019	0.020	0.021
D	15.100	15.400	15.700	0.594	0.606	0.618
D1	8.800	8.900	9.000	0.346	0.350	0.354
D2	2.730	2.800	2.870	0.107	0.110	0.113
E	9.900	10.000	10.100	0.390	0.394	0.398
E1	-	8.700	-	-	0.343	-
ΦP	3.570	3.600	3.630	0.141	0.142	0.143
ΦP1	1.400	1.500	1.600	0.055	0.059	0.063
e	2.54BSC			0.1BSC		
e1	5.08BSC			0.2BSC		
L	13.150	13.360	13.570	0.518	0.526	0.534
L1	7.35REF			0.29REF		
L2	2.900	3.000	3.100	0.114	0.118	0.122
L3	1.650	1.750	1.850	0.065	0.069	0.073
L4	0.900	1.000	1.100	0.035	0.039	0.043
Q1	5^0	7^0	9^0	5^0	7^0	9^0
Q2	5^0	7^0	9^0	5^0	7^0	9^0
Q3	5^0	7^0	9^0	5^0	7^0	9^0
Q4	1^0	3^0	5^0	1^0	3^0	5^0